	Application No. Applicant(s)			
Notice of Allowability	10/587,039	HOURAI ET AL.	OURALET AL	
	Examiner	Art Unit		
	Felisa C. Hiteshew	1792		
	relisa C. filestiew	1792		
The MAILING DATE of this communication appear All claims being allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIC of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate commu GHTS. This application is si	this application. If not include nication will be mailed in due of	d course. THIS	
1. This communication is responsive to the amendment filed of	on 11/20/2007.			
2. The allowed claim(s) is/are 3-5,7 and 8.				
3. 🗷 Acknowledgment is made of a claim for foreign priority und	der 35 U.S.C. § 119(a)-(d) o	r (f).		
a) ☑ All b) ☐ Some* c) ☐ None of the:		· ·		
1. Certified copies of the priority documents have	been received.			
2. Certified copies of the priority documents have	been received in Application	ı No		
Copies of the certified copies of the priority doc	uments have been received	in this national stage applicati	on from the	
International Bureau (PCT Rule 17.2(a)).				
* Certified copies not received:				
Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONMETHIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	of this communication to file ENT of this application.	a reply complying with the requ	uirements	
4. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which gives	tted. Note the attached EXA	MINER'S AMENDMENT or NO declaration is deficient.	OTICE OF	
5. CORRECTED DRAWINGS (as "replacement sheets") must	be submitted.			
(a) I including changes required by the Notice of Draftsperso		(PTO-948) attached		
1) 🗌 hereto or 2) 🔲 to Paper No./Mail Date				
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	Amendment / Comment or i	n the Office action of		
Identifying indicia such as the application number (see 37 CFR 1.8 each sheet. Replacement sheet(s) should be labeled as such in the	34(c)) should be written on the e header according to 37 CFF	e drawings in the front (not the l 1.121(d).	back) of	
 DEPOSIT OF and/or INFORMATION about the depos attached Examiner's comment regarding REQUIREMENT F 	it of BIOLOGICAL MATE OR THE DEPOSIT OF BIO	RIAL must be submitted. No LOGICAL MATERIAL.	ote the	
Attachment(s)	5 			
1. Notice of References Cited (PTO-892)		ormal Patent Application		
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. ☐ Interview Sui Paper No./N			
 Information Disclosure Statements (PTO/SB/08), Paper No./Mail Date <u>09/05/2007</u> 	7. 🗌 Examiner's A	mendment/Comment		
 Examiner's Comment Regarding Requirement for Deposit of Biological Material 		tatement of Reasons for Allow	ance	
	9.	Felisa C. Hiteshew Primary Examiner Art Unit: 1792	2	

U.S. Patent and Trademark Office PTOL-37 (Rev. 08-06) Art Unit: 1792

Information Disclosure Statement

The PTOL 1449 of 09/05/2007 has been received, reviewed and considered.

Allowable Subject Matter

1. Claims 3-5, 7 and 8 are allowed.

The following is an examiner's statement of reasons for allowance: The prior art of record does not teach nor render obvious the instantly claimed invention. There is no teaching in the art to perform the processes that are now claimed. The prior art previously cited does not teach a method for growing silicon single crystals, comprising pulling a Silicon single crystal by the CZ method in a hydrogen-containing inert gas atmosphere so as to expand the range of the pull rate for the PI region at which a single crystal containing no COPs or dislocation clusters throughout the crystal in the radial direction having an interstitial rich region can be pulled, wherein the pulling of the silicon single crystal is conducted at a pull rate within an expanded range of the pull rate for the PI region so as to grow a grown-in defect-free silicon single crystal having a body portion that is an interstitial rich region, and the composition of the hydrogencontaining inert gas atmosphere is set so that the hydrogen concentration VH (vol%), air concentration VAir (vol%) and argon concentration VAr (vol%), when indicated as points (VH, VAr, VAir) in appended Fig. 12, are values which lie within a non- combustion range-enclosed by point A (100,0,0), point B (0,100,0), point C (0,0,100), point D (4,0,96), point E (4,84,12) and point F (75,0,25). There is no motivation in the art to change the prior art's teaching of to arrive at the instantly claimed process.

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Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Felisa Hiteshew whose telephone number is (571) 272-1463. The examiner can normally be reached on Mondays through Thursday from 5:30 AM to 4:00 PM with Fridays off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael Barr, can be reached on (571) 272-1414. The fax phone number for the organization where this application or proceeding is assigned is (571) 273-1463.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system. see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866- 217-9197 (toll-free).

FELISA HITESHEW PRIMARY EXAMINER